

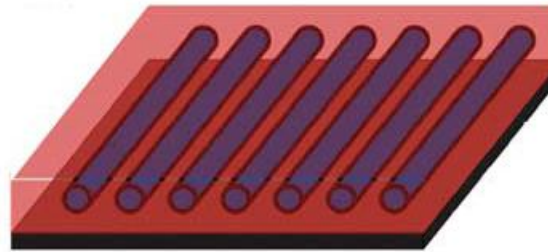
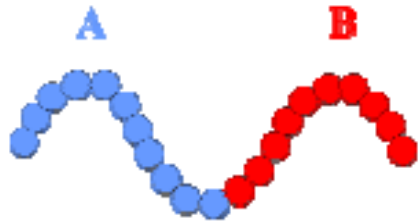
Directed Self-Assembly and Application in Nanomanufacturing

Rani S. Ghaida

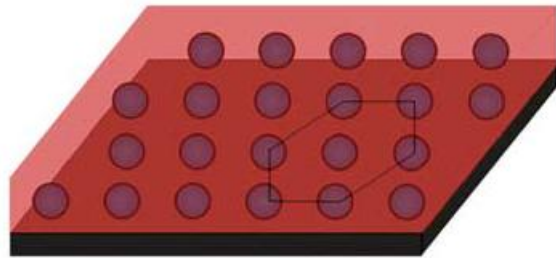
NanoCAD Lab, EE Dept., UCLA

rani@ee.ucla.edu

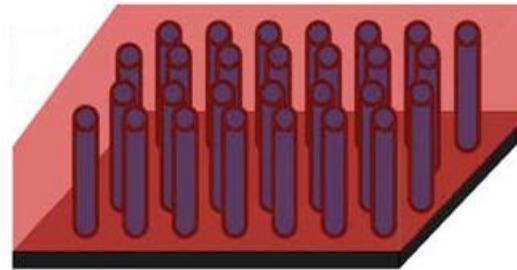
Self-Assembling Block Copolymers



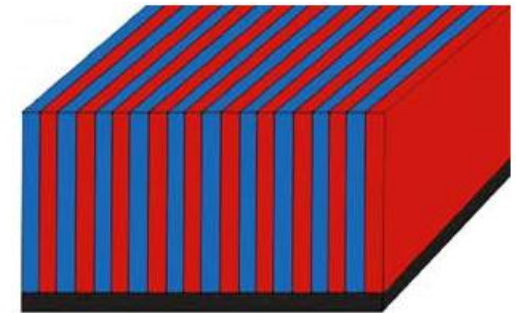
R. A. Segalman, 2005



Spheres



Cylinders

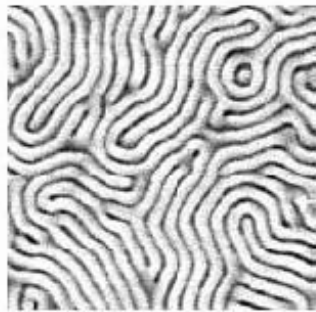


Lamellae

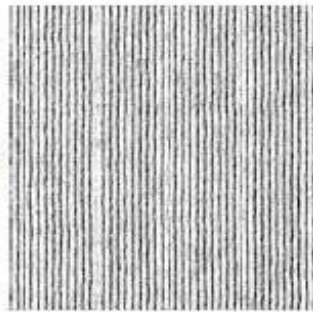
➔ *Increasing volume fraction*

- Block copolymer → 2 or more polymeric chains, covalently attached and chemically different
- Structures formed naturally at thermodynamic minima (with annealing)
- Controls: molecular weight, composition, interaction parameter
- Most common blocks: PS-PMMA → 25-50nm pitch
PS-PDMS → 14-45nm pitch

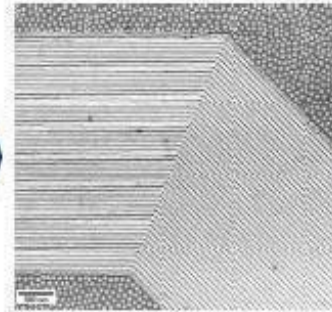
DSA and App for IC Manufacturing



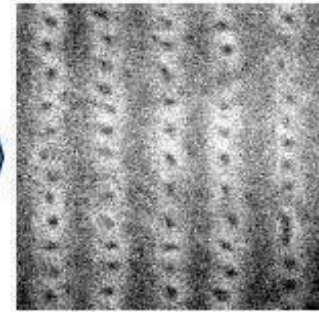
Naturally formed nanostructure with many defects



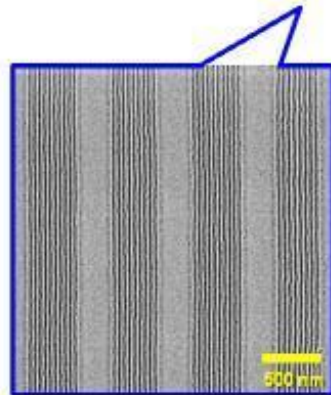
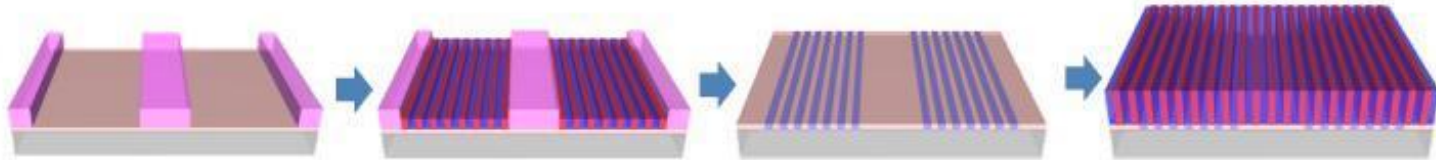
Epitaxial assembly for defect-free nanostructure
Nature, 424, 411, 2003



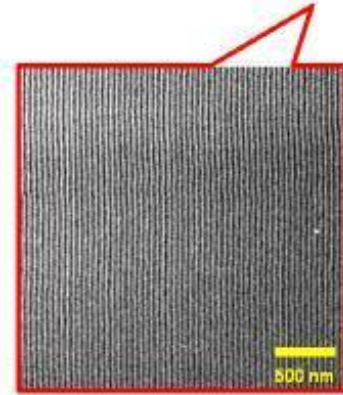
Directed assembly for device oriented nanostructure
Science, 308, 1442, 2005



Novel complex nanostructure
Adv.Mater. 19, 3171, 2007



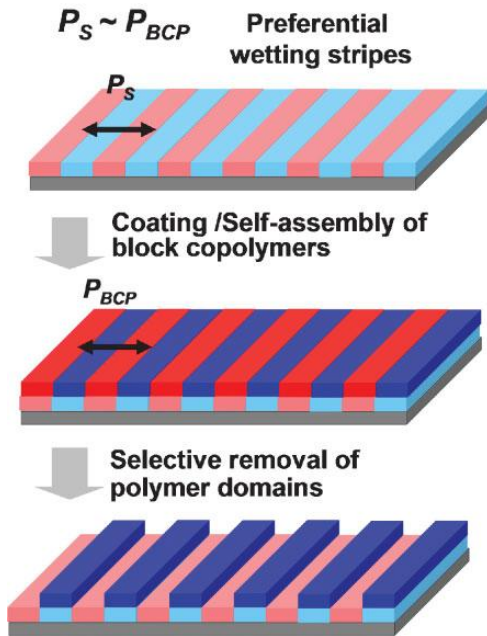
Soft Graphoepitaxy of Block Copolymer Assembly
Nano Letters 9, 2300, 2009



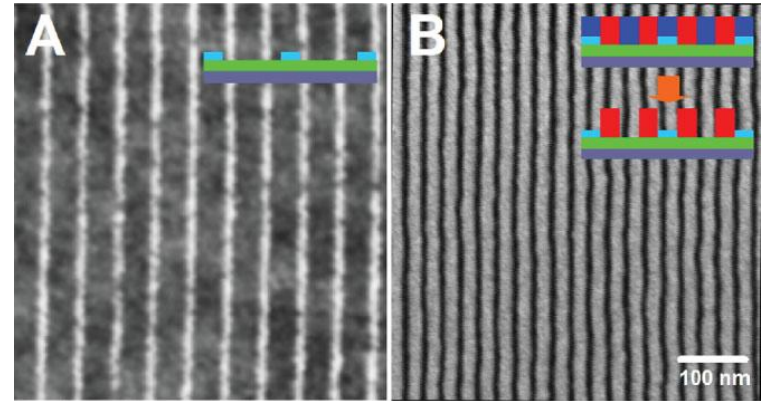
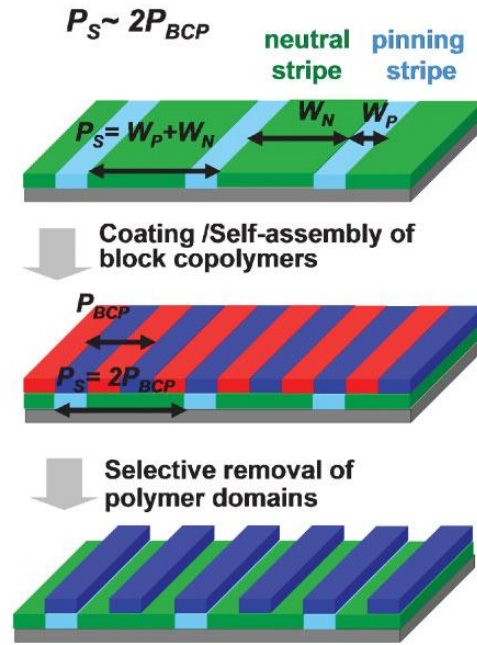
Ultralarge-Area Block Copolymer Lithography
ACS Nano 4, 5181, 2010

DSA and App for IC Manufacturing

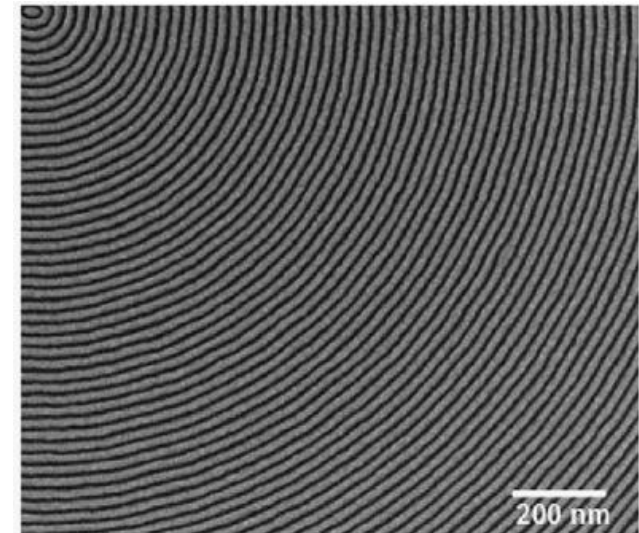
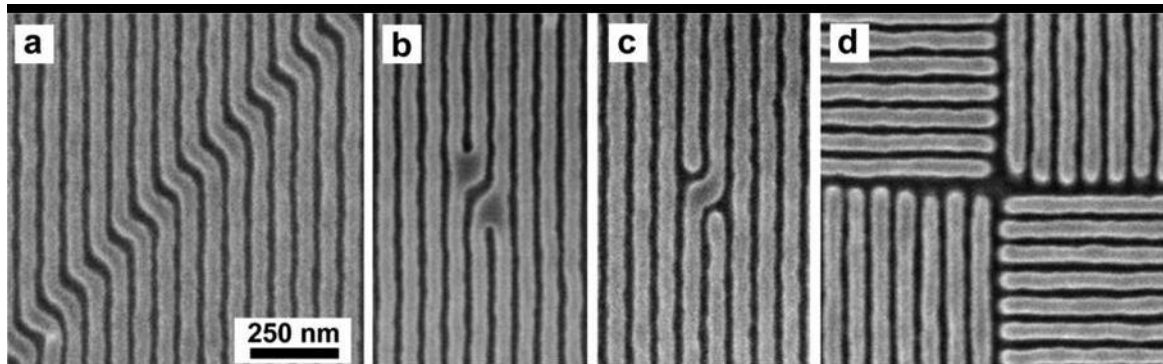
A) Dense Chemical Pattern



B) Sparse Chemical Pattern

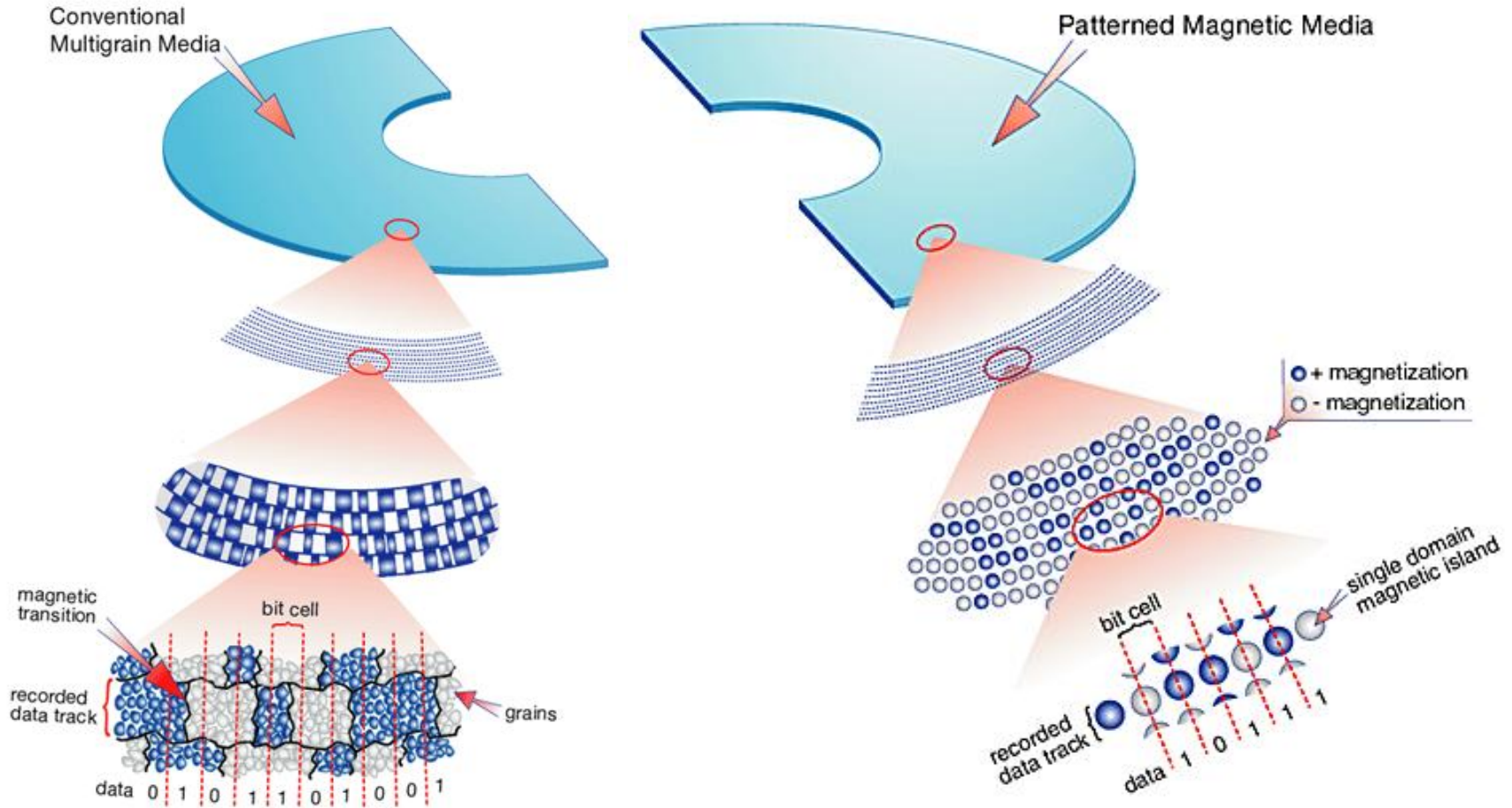


J. W. Cheng, 2008



Stoykovich, 2007

Application for Data Storage

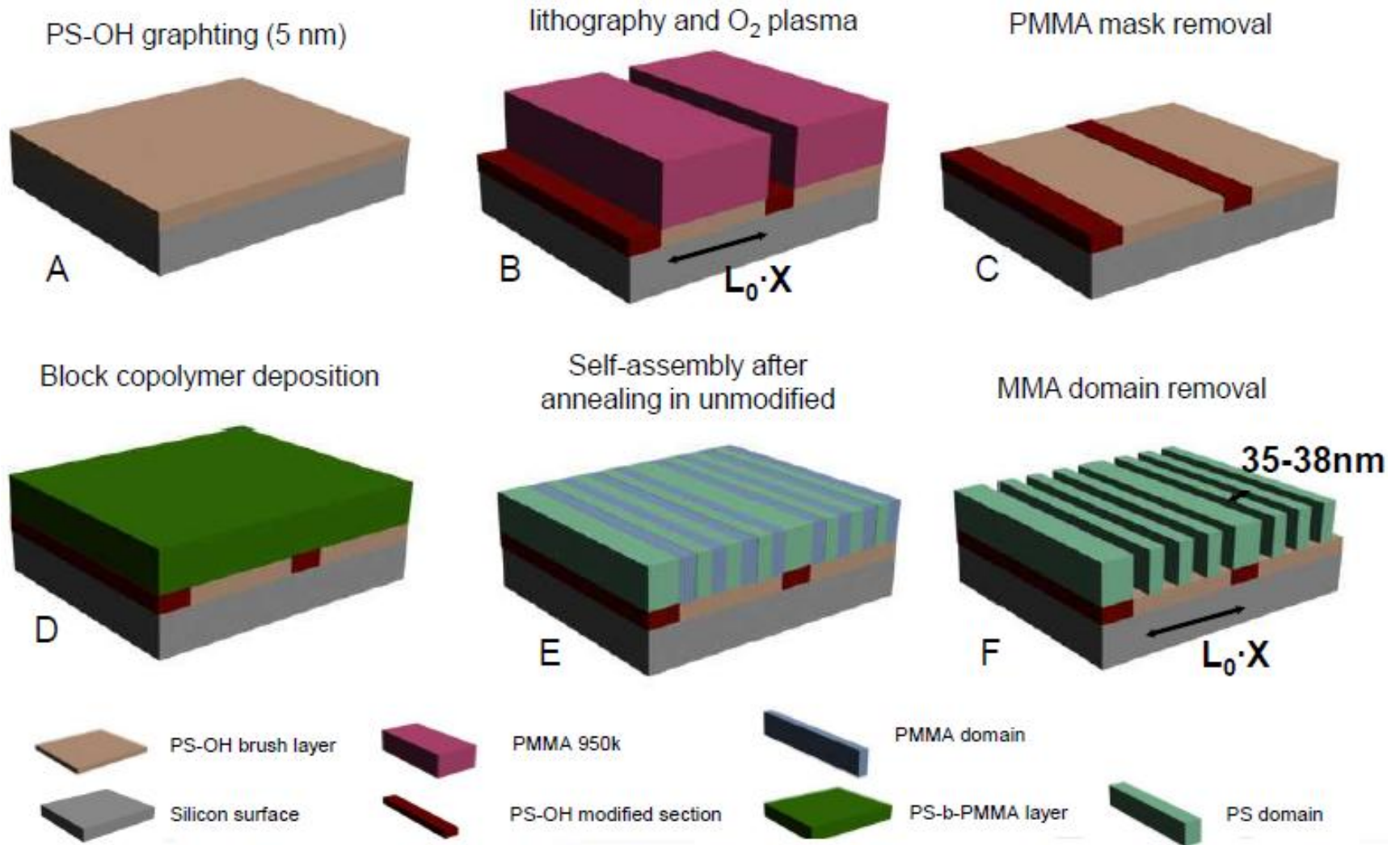


Hitachi Global Storage Technologies

Hitachi Global Storage Technologies

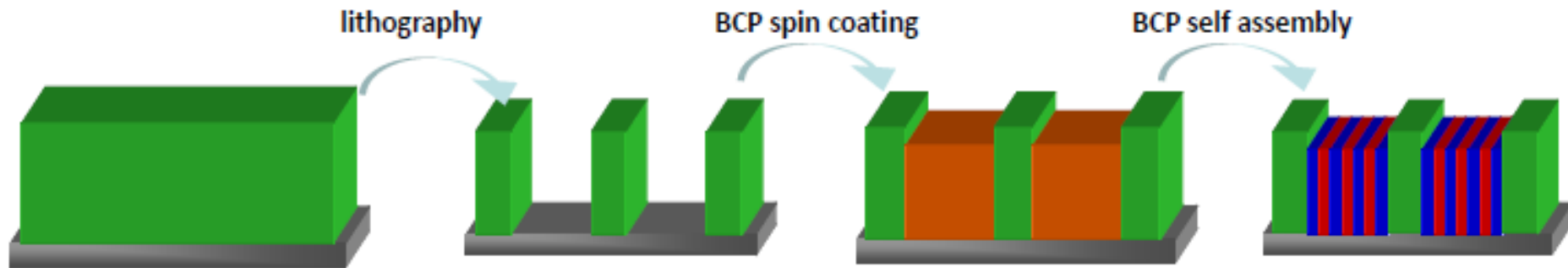
- Conventional way noisier with increasing density (need 100 grains/bit)
- DSA → 1 dot/bit → density increase by ~100X and thermally stable

Pattern Alignment – Chemical Surface Modification



R. Tiron, 2011

Pattern Alignment – Graphoepitaxy



- First litho patterns must be resistant to solvent & bake
- BCP orientation with respect to the substrate must be controlled
- More versatile process

R. Tiron, 2011

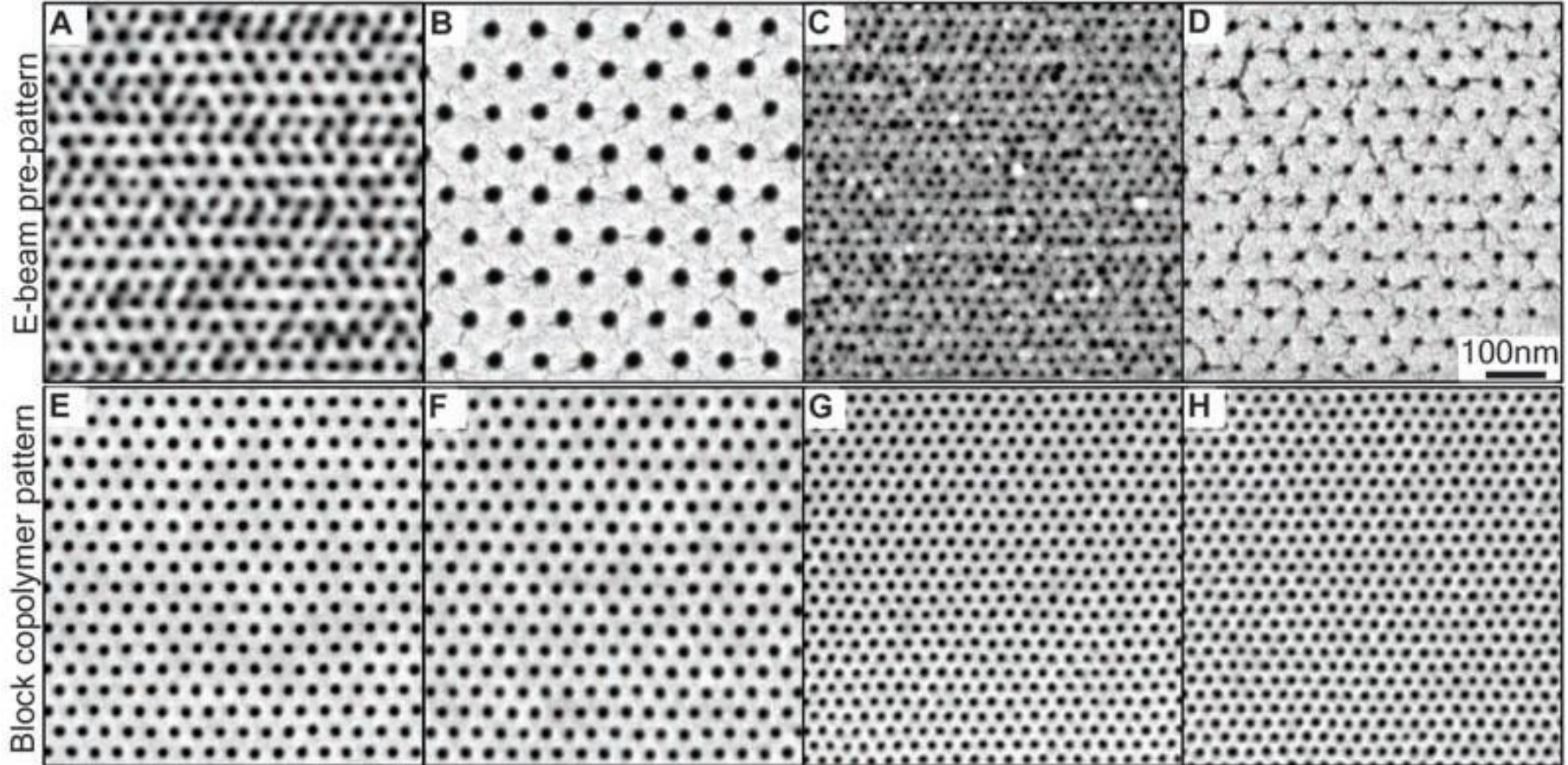
Pattern Multiplication and Rectification

Pattern Rectification
 $L_s=39\text{nm}$; $L_p=39\text{nm}$

Density Multiplication
 $L_s=78\text{nm}$; $L_p=39\text{nm}$

Pattern Rectification
 $L_s=27\text{nm}$; $L_p=27\text{nm}$

Density Multiplication
 $L_s=54\text{nm}$; $L_p=27\text{nm}$



DSA Benefits & Challenges

- Benefits
 - Density multiplication
 - Pattern rectification
 - Good for regular arrays of lines and vias
 - Improved LER (dependent on molecules sizes)
- Challenges
 - Difficult to ensure perfect patterning
 - Particle defects → larger impact than in litho
 - Limited patterns especially with density multiplication
 - Not good for isolated features
 - Design rules restrictions (e.g., no good control for spacing and width values)